ANTICORROSIVE MATERIAL FOR SEMICONDUCTOR FABRICATION

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Abstract of **JP10004083**

PROBLEM TO BE SOLVED: To provide an anticorrosive material having a higher corrosion resistance than SiO2 , Al2 O3 , AlN, etc.
SOLUTION: A part of a product to be exposed to a fluoric corrosive gas such as SF6 , CF4 , CHF3 , ClF3 and HF or its plasma is made from a compd. thin film or single crystal. The product is e.g. a Si wafer clamp ring, upper electrode shield ring, or inner wall of a plasma treating apparatus, etching apparatus, etc., for the semiconductor fabrication. The compd. is an oxide, nitride, carbide or fluoride of 3a elements on the periodic table, e.g. Sc, La, Ce, Eu and Dy.